

Charge Collection and Field Profile Studies in Heavily Irradiated Silicon Strip Sensors for the ATLAS Inner Tracker Upgrade



K. Hara, HSTD10, Xi'an China, 25-29 Sep 2015

ATLAS ITk Lol Layout and Fluence at HL-LHC

Fluence evaluations per 3000 fb⁻¹ 1 MeV neutron equivalent fluence



ATLAS12 design



Irradiation

Neutron irradiation: Ljubljana reactor Pion irradiation: Proton irradiations: Karlsruhe 23 MeV

An sruhe 23 MeV All damages translated Birmingham 27 MeV to 1-MeV nea NIEL factori YRIC 70 MeV os Alamos 200

Irradiation example: CYRIC (Tohoku Univ) Scan box: 15 sample slots





Sample holder/slot (11x11cm opening)

Al²⁷(p, 3pn)Na²⁴ Al foils for dosimetry

CYRIC case: For 10¹²~10¹⁶/cm² range irradiation, A few min ~6 hrs at beam current $10nA^{1}\mu A$

Charge Collection Measurement Consistency



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Long term annealing at 60°



A07 (neutron) studied previously => behavior similar to A12M I. Mandic et al., NIMA 629 (2011) 101

All data shown below are after controlled annealing of 80min @ 60°C

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20000

15000

10000

5000

* V = 1400 V

10³

Time at 60°C (min)

 10^{2}

10

ATLAS12A+ATLAS07 Neutron irradiation



ATLAS12A proton irradiations



ATLAS12A-12M proton irradiations



12M yields larger signal at low fluence and at low bias: different initial resistivity

Testbeam setup at DESY 4.4 GeV electrons

Two sets of 3 tracking planes (Mimosa26)

Sample w/ Alibava readout Cooling achieved by silicone oil (piping not shown)

Source vs testbeam (DESY 4.4-GeV electrons)



Source vs testbeam (DESY 4.4-GeV electrons)



Source vs beam:

Charge distributions in reasonable agreement Cluster Size slightly wider for source as expected

Fluence dependence (all A12A data points)



Fluence dependence

A12A yield slightly smaller & n-damage is larger at low fluence and low bias => becomes similar at large fluence after 80min@60°C annealing 25 proton irradiation neutron irradiation Vb=300V 20 Collected Charge (ke) Collected Charge (ke) × A07 @900V A12A@300V A12A@900V 5 A07 @300V A07 @500V A12A@500V A12M@300V 0 0 1.0E+14 1.0E+15 1.0E+16 25 25 proton irradiation proton irradiation Vb=900V Vb=500V 20 20 Collected Charge (ke) ŧ, Collected Charge (ke) A12A@900V A07 @900V A12A@500V 5 A12M@900V 5 A107 @500V -n A12A 900V A12M@500V -n A12A 500V 0 0 1.0E+14 1.0E+15 1.0E+16 1.0E+14 1.0E+15 1.0E+16 Fluence (1-MeV n_{oa}/cm^2) / 21 **E** 1 14 84 31

S/N at HL-LHC

Barrel short (24mm)strips up to : 1.1×10^{15} /cm² Barrel long (48mm) strips up to : 0.6×10^{15} /cm² Endcap (8-48mm) strips: max 1.6×10^{15} /cm²





At Vb=500V, strip detectors remain as precision tracker after HL-LHC fluence

Charge collection of samples irradiated with p/n/ π



Different CCE curves measured for the same NIEL fluence Investigated E-field profile using e-TCT technique

edge TCT (transient current technique)



<u>e-TCT</u> non-irradiated samples

Charge vs. depth

• A12A detector depleted at 350 V (A07 deplete at 200V)



active depth ~ 305/295 μm
A12A about 10 μm more than
A07 →as expected from physical thicknesses
(320/310 μm for A12A/A07)

Velocity profile

$I(y, t \sim 0) \approx qE_w(y) \left[\overline{v}_e(y) + \overline{v}_h(y) \right] \propto E; \quad \overline{v}_e(y) + \overline{v}_h(y) \propto E$

• induced current at $t \sim 0$ proportional to carrier velocity and weighting field at laser spot location

($E_{\mu\nu}$ ~ constant, see: G. Kramberger, et al., IEEE TNS NS-57 (2010) 2294.)

• if *E* not too large, *I* proportional to e-filed *E*

at 200 V A07 depleted, A12A not depleted

• plots normalized to same integral from 0-300 μ m (because [Edx = Bias)



 \rightarrow expected depletion depth for A12A at 200 V 220 μ m!

Edge-TCT with detectors irradiated in Ljubljana (neutron)



• larger field near back plane in A07

ightarrow roughly in agreement with expectation because of different initial resistivities



Edge-TCT with detectors irradiated by protons/neutrons/pions





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consistent with CCE measurements

→ more CC after charged particle irradiation
 → more CC for pions than for 23 MeV protons:
 → larger *E* field at back side after pion irrad than after 23 MeV proton irradiation.

At moderate bias, CC is least after neutron irradiation

Summary

1. CC of HPK p-bulk sensors irradiated with protons and neutrons are evaluated extensively with β -ray by several institutions in collaboration

CC of >9 Ke⁻ can be maintained at Vb=500V after 1.6×10^{15} 1-MeV n_{eq}/cm²

- S/N> 19 for short strips (L=2.4cm) after 1.1x10¹⁵ 1-MeV n_{eq}/cm²
- S/N> 18 for long strips (L=4.8cm) after 0.6x10¹⁵ 1-MeV n_{eq}/cm²
- S/N> 14 for innermost EC after 1.6x10¹⁵ 1-MeV n_{eq}/cm²
- 2. β -ray measurements are validated by beam
- 3. Difference in p/n/pion damages investigated in terms of electric-field profiles using e-TCT
 - Reduction in the charge collection due to induced traps
 - Change in the field profile across depth due to generated currents Both dependent on the irradiation particles (n/p/π)
 ✓ Defect introduction rates are more in the order of : n>p>π
 ✓ Differences in E-filed profile shapes due to double peak E-field:

 \Rightarrow HPK p-bulk strip sensors are operational at the HL-LHC fluence

Edge-TCT with detectors irradiated by protons/neutrons/pions



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Double Peak E-field V. Eremin et al. NIMA535 (2004)622.

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$$\rho_{eff} = \rho_{dopants} \sim -eN_A \qquad ... \text{ space-charge density}$$

$$\rho_{eff} = e(f_D n_D - f_A n_A) + \rho_{dopants}$$
radiation induced trapping levels with occupancies f



Edge-TCT with detectors irradiated in Karlsruhe (p 23 MeV)



larger active volume after irradiation with 23 MeV protons than after neutrons at 500 V
 → consistent with larger charge measured with Alibava



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